

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1-11. (canceled).

12. (currently amended): A gallium nitride-based compound semiconductor light-emitting device comprising ~~the~~ a transparent positive electrode according to claim 1, having a contact metal layer in contact with a p-type semiconductor layer, a current diffusing layer on the contact metal layer, the current diffusing layer having an electrical conductivity larger than that of the contact metal layer, and a bonding pad layer on the current diffusing layer, wherein the thickness of the contact metal layer is from 0.1 to 7.5 nm.

13. (new): The gallium nitride-based compound semiconductor light-emitting device according to claim 12, wherein the contact metal layer is a platinum group metal or an alloy containing a platinum group metal.

14. (new): The gallium nitride-based compound semiconductor light-emitting device according to claim 13, wherein the contact metal layer is platinum.

15. (new): The gallium nitride-based compound semiconductor light-emitting device according to claim 12, wherein the thickness of the contact metal layer is from 0.1 to 5 nm.

16. (new): The gallium nitride-based compound semiconductor light-emitting device according to claim 15, wherein the thickness of the contact metal layer is from 0.5 to 2.5 nm.

17. (new): The gallium nitride-based compound semiconductor light-emitting device according to claim 12 wherein the current diffusing layer is a metal selected from the group consisting of gold, silver and copper, or an alloy containing at least one member of gold, silver and copper.

18. (new): The gallium nitride-based compound semiconductor light-emitting device according to claim 17, wherein the current diffusing layer is gold.

19. (new): The gallium nitride-based compound semiconductor light-emitting device according to claim 12, wherein the thickness of the current diffusing layer is from 1 to 20 nm.

20. (new): The gallium nitride-based compound semiconductor light-emitting device according to claim 19, wherein the thickness of the current diffusing layer is from 1 to 10 nm.

21. (new): The gallium nitride-based compound semiconductor light-emitting device according to claim 20, wherein the thickness of the current diffusing layer is from 3 to 6 nm.